MTM763200LBF

Panasonic

MTM763200LBF

Silicon N-channel MOSFET (FET1) Silicon P-channel MOSFET (FET2)

For Switching For DC-DC Converter

■ Features

- Low Drain-source On-state Resistance : RDS(on)typ. N-ch = 80 mΩ(VGS = 4.0 V) P-ch:100 mΩ (VGS = -4.0 V)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL : Level 1 compliant)
- Marking Symbol JB
- Basic Part Number Nch+Pch MOS 20V (Individual)

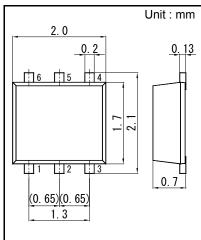
■ Packaging

Established: 2008-03-07

Revised

: 2013-10-17

Embossed type (Thermo-compression sealing) 3 000 pcs / reel (standard)



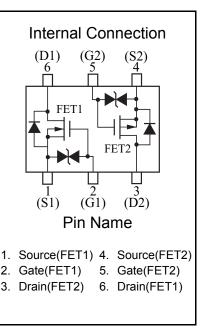
- 1. Source(FET1) 4. Source(FET2)
- 2. Gate(FET1) 5. Gate(FET2)
- 3. Drain(FET2) 6. Drain(FET1)

Panasonic	WSMini6-F1-B
JEITA	SC-113DA
Code	_

■ Absolute Maximum Ratings Ta = 25 °C

	Parameter	Symbol	Rating	Unit
	Drain-source Voltage	VDS	20	V
	Gate-source Voltage	VGS	±10	V
	Drain current	ID	1.9	Α
	Peak drain current	IDp	12	Α
	Drain-source Voltage	VDS	-20	V
	Gate-source Voltage	VGS	±10	V
	Drain current	ID	-1.2	Α
	Peak drain current	IDp	-7	Α
'	Total power dissipation *1	PD	700	mW
Overall	Channel temperature	Tch	150	°C
	Operating ambient temperature	Topr	-40 to +85	°C
	Storage Temperature Range	Tstg	-55 to +150	°C

Note *1 Measuring on ceramic substrate at 40 mm \cdot 38 mm \cdot 0.2 mm. PD absolute maximum rating Non-heat sink: 150 mW.



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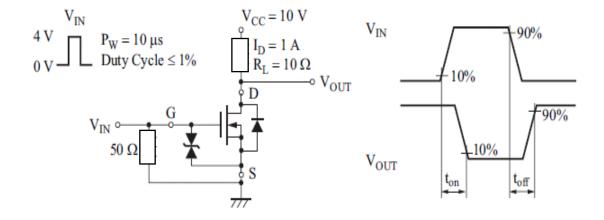
■ Electrical Characteristics Ta = 25 °C ± 3 °C FET1 (N-ch.)

1 E 1 1 (14 C11.)						
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = 1.0 mA, VGS = 0 V	20			V
Zero Gate Voltage Drain Current	IDSS	VDS = 20 V, VGS = 0 V			1.0	μA
Gate-source Leakage Current	IGSS	$VGS = \pm 8.0 \text{ V}, VDS = 0 \text{ V}$			±10	μA
Gate-source Threshold Voltage	Vth	ID = 1.0 mA, VDS = 10 V	0.4	0.85	1.3	V
Drain-source ON resistance *1	RDS(ON)1	ID = 1.0 A, VGS = 4.0 V		80	105	mΩ
Drain-source ON resistance	RDS(ON)2	ID = 0.5 A, VGS = 2.5 V		100	150	
Forward transfer admittance *1	Yfs	ID = 1.0 A, VDS = 10 V	3.0			S
Input Capacitance	Ciss			280		
Output Capacitance	Coss	VDS = 10 V, VGS = 0, f = 1 MHz		18		pF
Reverse Transfer Capacitance	Crss			17		
Turn-on time *2	ton	VDD = 10 V, VGS = 0 to 4 V,		12		
Turn-on time	ton	ID = 1.0 A				
Turn-off time *2	toff	VDD = 10 V, VGS = 4 to 0 V,		50		ns
rum-on ume	lon	ID = 1.0 A		30		

Note: 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

2. *1 Pulse measurement

*2 Measurement circuit for Turn-on Time / Turn-off Time



Doc No. TT4-EA-10567

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Revision. 2

MOS FET

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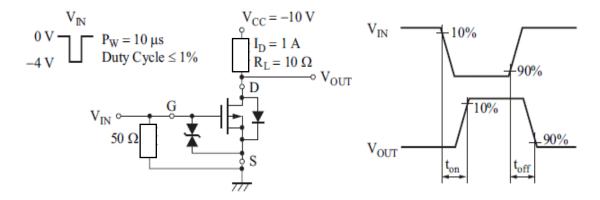
FET2 (P-ch.)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = -1 mA, VGS = 0 V	-20			V
Zero Gate Voltage Drain Current	IDSS	VDS = -20 V, VGS = 0 V			-1.0	μA
Gate-source Leakage Current	IGSS	$VGS = \pm 8 \text{ V}, VDS = 0 \text{ V}$			±10	μΑ
Gate-source Threshold Voltage	Vth	ID = -1.0 mA, VDS = -10 V	-0.4	-0.85	-1.3	V
Drain-source On-state Resistance *1	RDS(ON)1	ID = -1.0 A, VGS = -4.0 V		100	130	mΩ
	RDS(ON)2	ID = -0.6 A, VGS = -2.5 V		130	200	
Forward transfer admittance *1	Yfs	ID = -1.0 A, VDS = -10 V	3.0			S
Input Capacitance	Ciss			440		
Output Capacitance	Coss	VDS = -10 V, VGS = 0, f = 1 MHz		40		pF
Reverse Transfer Capacitance	Crss			38		
Turn-on Time *2	ton	VDD = -10 V, VGS = 0 to -4 V		35		
		ID = -1 A		33		ns
T *2	toff	VDD = -10 V, VGS = -4 to 0 V		100		
Turn-off Time *2		ID = -1 A		100		

Note: 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

2. *1 Pulse measurement

*2 Measurement circuit for Turn-on Time / Turn-off Time



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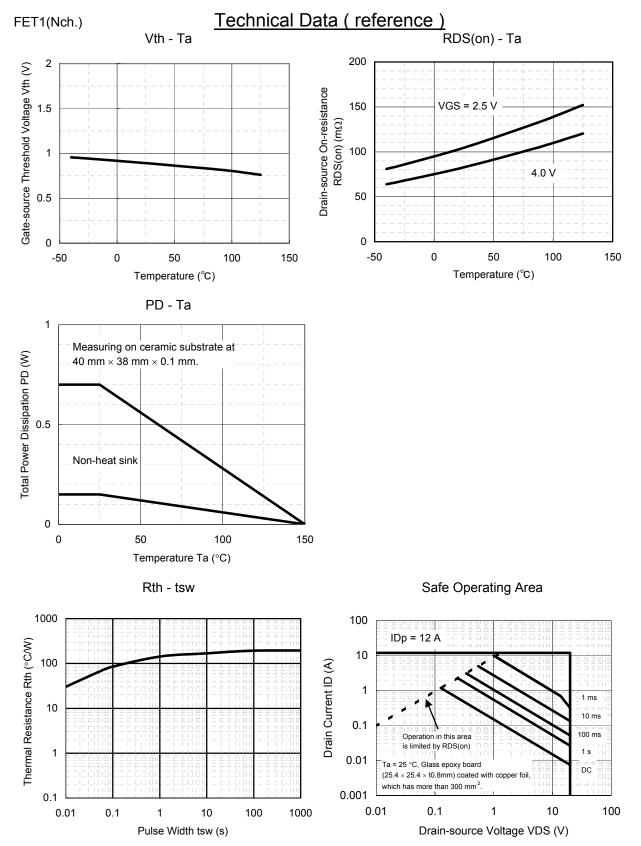
Technical Data (reference) FET1(Nch.) ID - VDS ID - VGS 1.5 1.5 VGS = 4.0 V Drain Current ID (A) Drain current ID (A) 9.0 2.0 V Ta = 85 °C 25 ℃ 1.5 V - 40 °C 0 0 0.1 0.2 0.3 0 0.5 2 1.5 Drain-source Voltage VDS (V) Gate-source voltage VGS (V) VDS - VGS RDS(on) - ID 1000 0.6 Drain-source On-state Resistance RDS(on) (mΩ) Drain-source Voltage VDS (V) 0.5 0.4 0.5 A 2.5 V 0.3 ID = 1.0 A VGS = 4.0 V 0.2 0.1 0 10 2 0 3 0.1 6 Drain Current ID (A) Gate-source Voltage VGS (V) Capacitance - VDS 1000

1000

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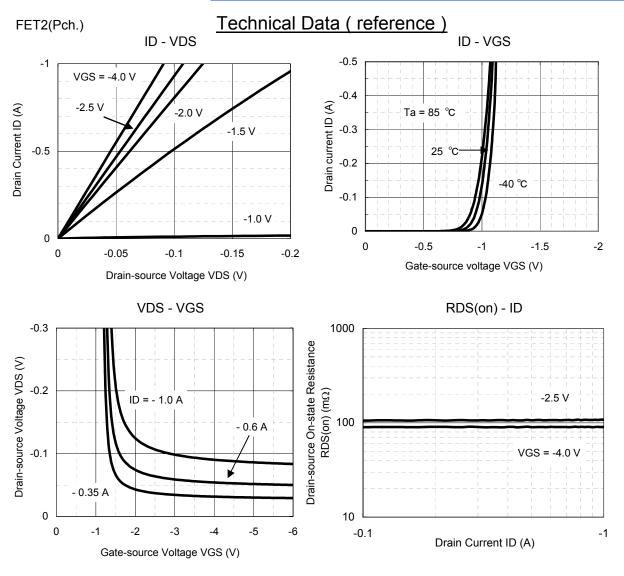
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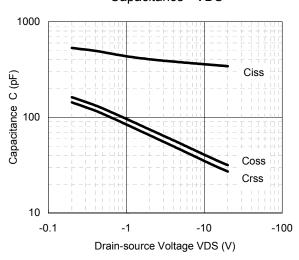
Page 5 of 8

MTM763200LBF

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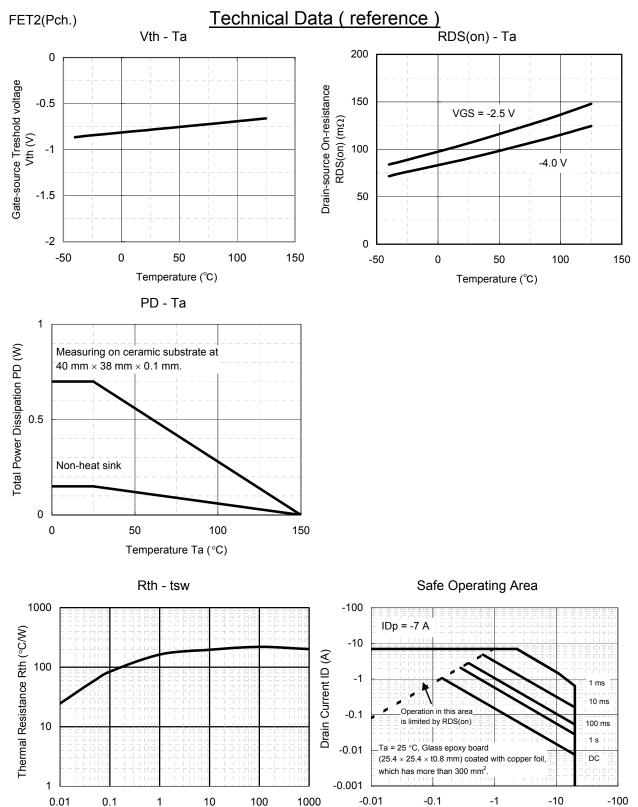


Capacitance - VDS



MTM763200LBF





Page 7 of 8

Drain-source Voltage VDS (V)

Established: 2008-03-07 Revised: 2013-10-17

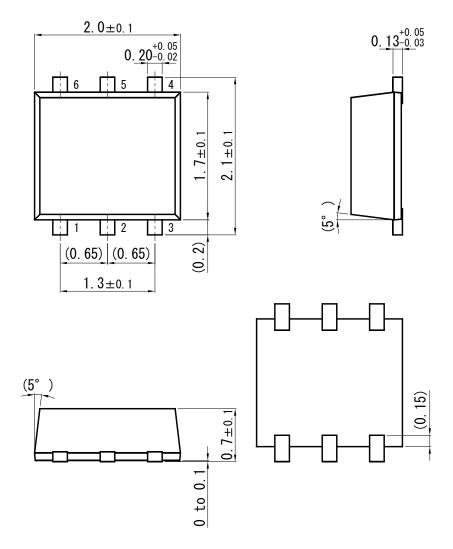
Pulse Width tsw (s)

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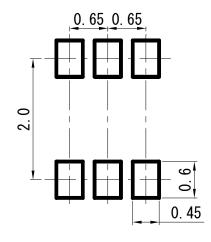
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Unit: mm



■ Land Pattern (Reference) (Unit: mm)



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